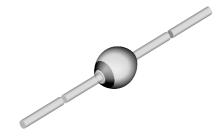


# BYM26C

Sintered Glass Junction, Ultrafast Avalanche Rectifier

VOLTAGE: 600V CURRENT: 2.3A



# **Features**

Glass passivated
High maximum operating temperature
Low leakage current
Excellent stability
Guaranteed avalanche energy absorption capability

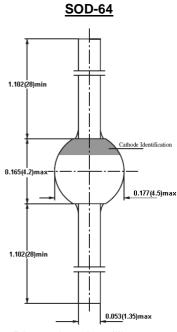
### **Mechanical Data**

Case: SOD-64 sintered glass case

Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C

Polarity: color band denotes cathode end

Mounting position: any



Dimensions in millimeters

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	SYMBOL	BYM26C	units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	600	V
Maximum RMS Voltage	$V_{RMS}$	420	V
Maximum DC blocking Voltage	$V_{DC}$	600	V
Reverse Breakdown Voltage at I <sub>R</sub> = 0.1mA	$V_{(BR)R}$	700min	V
Maximum Average Forward Rectified Current and Ttp=55°C; lead length=10mm	I <sub>FAV</sub>	2.3	А
Peak Forward Surge Current at t=10ms half sine wave	I <sub>FSM</sub>	45	А
Maximum Forward Voltage at Rated Forward Current and 25°C $I_F = 2.0A$	V <sub>F</sub>	2.65	V
Maximum DC Reverse Current $Ta = 25^{\circ}C$ at rated DC blocking voltage $Ta = 150^{\circ}C$	I <sub>R</sub>	10 150	μА
Maximum Reverse Recovery Time (Note 1)	Trr	30	nS
Non Repetitive Reverse Avalanche Energy	E <sub>R</sub>	10	mJ
Diode Capacitance at f=1MHz,V <sub>R</sub> =0V	C <sub>d</sub>	85	pF
Typical Thermal Resistance (Note 2)	R <sub>th(ja)</sub>	75	K/W
Storage and Operating Junction Temperature	Tstg, Tj	-65 to +175	$^{\circ}$

#### Note:

- 1. Reverse Recovery Condition  $I_F = 0.5A$ ,  $I_R = 1.0A$ ,  $I_{RR} = 0.25A$
- 2. Device mounted on an epoxy-glass printed-circuit board, 1.5mm thick; thickness of Cu-layer ≥40 μ m



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### **RATINGS AND CHARACTERISTIC CURVES BYM26C**

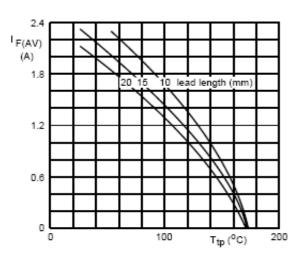


Fig.1 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).

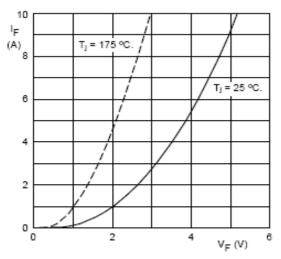


Fig. 3 Forward current as a function of forward voltage; maximum values.

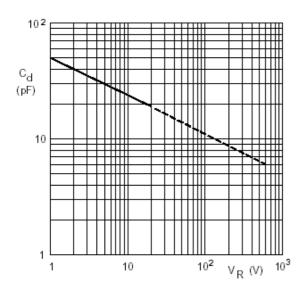


Fig.5 Diode capacitance as a function of reverse voltage; typical values.

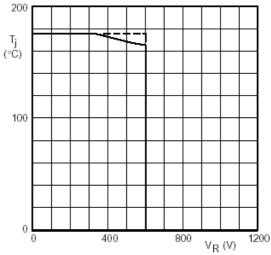


Fig. 2 Maximum permissible junction temperature as a function of reverse voltage.

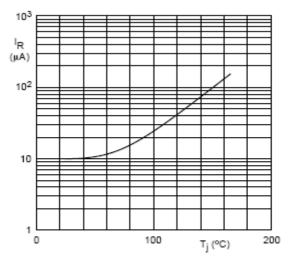


Fig.4 Reverse current as a function of junction temperature; maximum values.